

## Supporting Information

### Contrasting roles of Bi- doping and Bi<sub>2</sub>Te<sub>3</sub> alloying on the thermoelectric performance of SnTe

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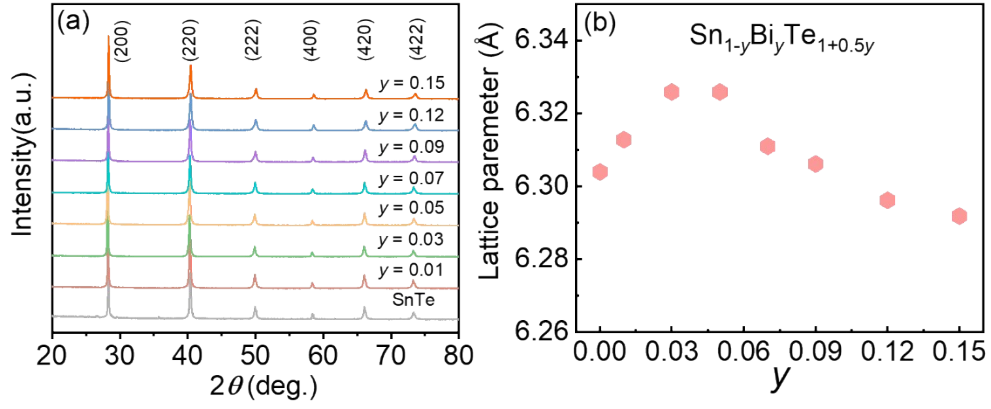
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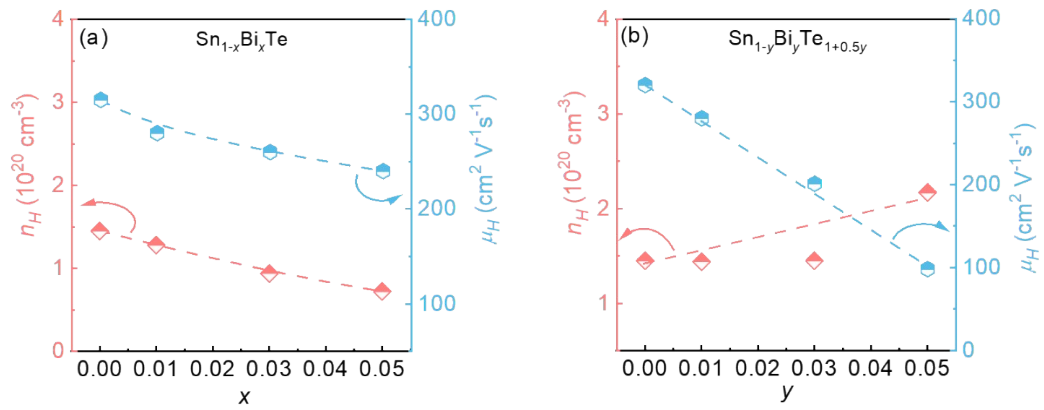
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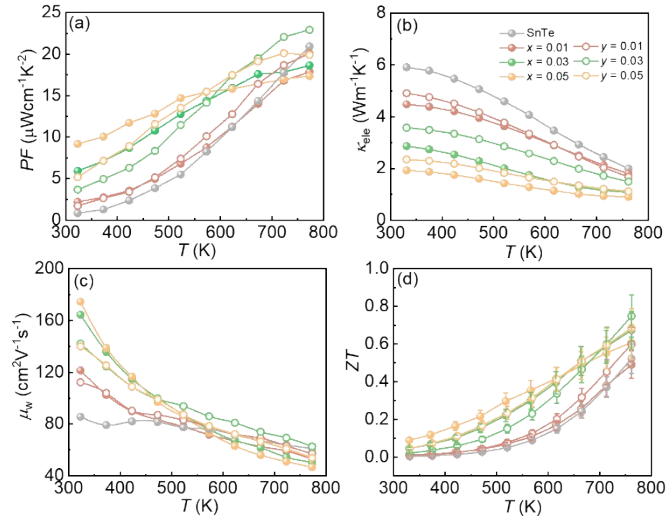
E-mails: [l.jin@fz-juelich.de](mailto:l.jin@fz-juelich.de), [yangzp@snnu.edu.cn](mailto:yangzp@snnu.edu.cn), [wud@snnu.edu.cn](mailto:wud@snnu.edu.cn).



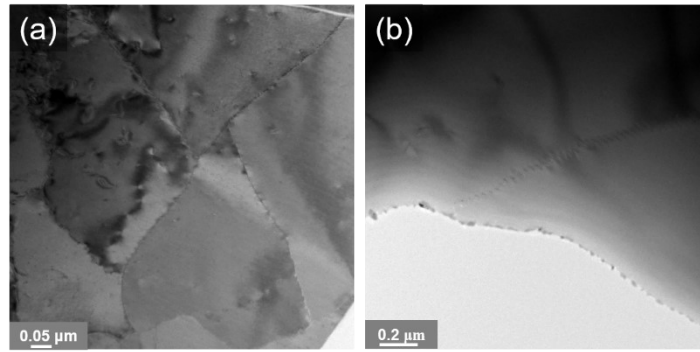
**Figure S1** (a) The powder XRD patterns for  $\text{Sn}_{1-y}\text{Bi}_y\text{Te}_{1+0.5y}$  ( $y = 0, 0.01, 0.03, 0.05, 0.07, 0.09, 0.12, 0.15$ ). (b) Calculated lattice parameters obtained from (a).



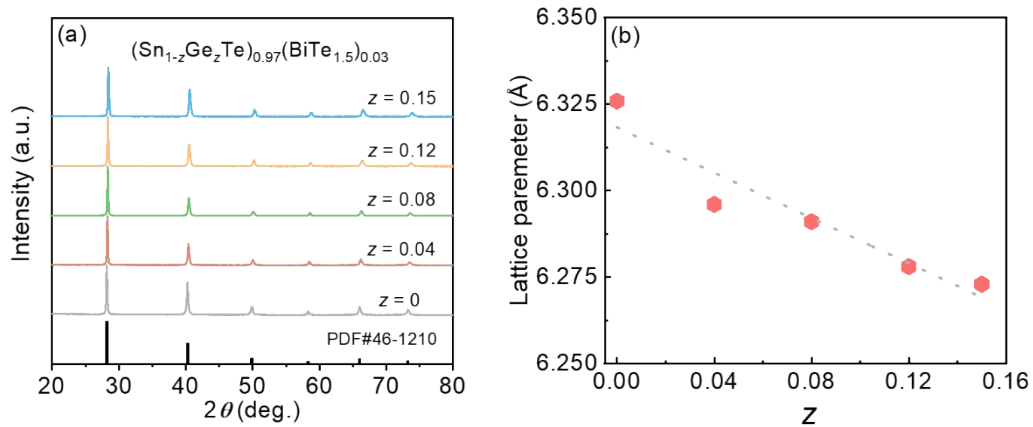
**Figure S2** (a) and (b) Room-temperature carrier concentration ( $n_H$ ) and carrier mobility ( $\mu_H$ ) of  $\text{Sn}_{1-x}\text{Bi}_x\text{Te}$  and  $\text{Sn}_{1-y}\text{Bi}_y\text{Te}_{1+0.5y}$ , respectively.



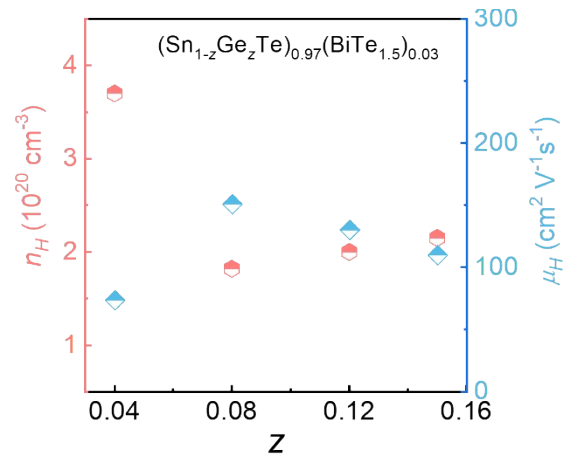
**Figure S3** Temperature dependent (a) power factor, (b) calculated electronic thermal conductivity, (c) calculated weighted carrier mobility, and (d)  $ZT$  of  $\text{Sn}_{1-x}\text{Bi}_x\text{Te}$  ( $x = 0, 0.01, 0.03$  and  $0.05$ ) and  $\text{Sn}_{1-y}\text{Bi}_y\text{Te}_{1+0.5y}$  ( $y = 0, 0.01, 0.03$  and  $0.05$ ).



**Figure S4** Low magnification TEM image of  $\text{Sn}_{0.97}\text{Bi}_{0.03}\text{Te}_{1.015}$  sample showing (a) mesoscale grains and (b) dislocation arrays at grain boundaries.



**Figure S5** (a) The powder X-ray diffraction (XRD) patterns and (b) calculated lattice parameters of  $(\text{Sn}_{1-z}\text{Ge}_z\text{Te})_{0.97}(\text{BiTe}_{1.5})_{0.03}$  ( $z = 0, 0.04, 0.08, 0.12$  and  $0.15$ ).



**Figure S6** Room-temperature carrier concentration ( $n_H$ ) and carrier mobility ( $\mu_H$ ) of  $(\text{Sn}_{1-z}\text{Ge}_z\text{Te})_{0.97}(\text{BiTe}_{1.5})_{0.03}$  ( $z = 0.04, 0.08, 0.12$  and  $0.15$ ).